L Number	Hits	Search Text	DB	Time stamp
1	571	(438/15).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/04 12:43
2	2	438/15 and (microdisplay or (micro near10 display))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/04 12:43
-	2	"6330099"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/26 13:26
-	2	"6362861"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/02 10:29
-	2231	"Agilent Technologies".AS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/02 10:36
-	0	"Agilent Technologies".AS. and 349/190	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/02 10:37
-	0	"anistropic etch" adj "filling hole"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/02 10:46
-	0	"anistropic etch" adj "liquid crystal filling hole"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/02 10:47
-	0	"anistropic etch" adj "liquid crystal"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/02 10:48
-	153	(349/190).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/02 15:20
-	440	(438/30).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/02 12:46
-	1	"anisotropic etch" adj "silicon wafer"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/02 12:55
-	3	"anisotropic etch" near "silicon wafer"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/02 12:56

-	61	"anisotropic etching" adj "silicon wafer"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/02 13:14
-	0	"anisotropic etching" near "liquid crystal"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/02 13:15
-	0	"anisotropic etching" near "liquid crystal substrate"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/02 13:15
-	708	"anisotropic etching" near "substrate"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/02 13:23
-	144	(349/154).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/02 13:26
-	10	"injection hole" adj "substrate"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/02 18:05
-	0	"sealant" adj "glue, epoxy, solder"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/02 13:46
-	0	"sealant material" adj "glue, epoxy,and solder"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/02 13:46
-	311	"sealant" adj "epoxy"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/02 13:54
-	3	"liquid crystal" adj "microdisplays"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/02 14:22
-	83	"testing" adj "liquid crystal display"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/02 14:29
-	0	"testing" adj "liquid crystal micro display"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/02 14:27
-	0	"testing" adj "sealing hole"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/02 14:29

-		0	"testing" adj " liquid crystal sealing hole"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/02 14:30
-		2	"6330099"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/02 15:09
-		0	(349/190 and testing).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/02 15:18
-		0	349/190 adj testing	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/02 15:18
-		0	349/190 near testing	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/02 15:18
-		0	"349/190" near "testing"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/02 15:18
-		0	"349/190" adj "testing"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/02 15:18
-		475	(438/15).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/02 15:21
-		98	(injection hole) adj (glue)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/02 16:19
-		32	"sealant material" adj "epoxy"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/02 16:30
-		0	"liquid crystal" adj "sealant material" adj "epoxy"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/02 16:30
-		0	"liquid crystal" adj "sealant material"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/02 16:31
-		3	"liquid crystal" near "sealant material"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/02 16:31

-	7	"6177288"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/02 18:05
-	21	(liquid adj crystal) near10 (micro adj displays)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/26 13:35
-	4	liquid adj crystal adj micro-displays	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/26 13:36
-	7	liquid adj crystal adj micro adj displays	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/26 13:37
-	1078	(plurality adj holes) near10 substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/26 13:40
-	129	(liquid adj crystal) near10 (injection adj holes)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/26 15:34
-	0	((liquid adj crystal) near10 (micro adj displays)) and (liquid adj crystal adj micro-displays) and (liquid adj crystal adj micro adj displays) and ((liquid adj crystal) near10 (injection adj holes))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/26 14:39
-	4	((liquid adj crystal) near10 (micro adj displays)) and (liquid adj crystal adj micro-displays) and (liquid adj crystal adj micro adj displays)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/26 14:40
-	0	((liquid adj crystal) near10 (micro adj displays)) and ((liquid adj crystal) near10 (injection adj holes))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/26 14:50
-	7	"6177288"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/26 16:03
-	0	(seal) near10 (glue and epoxy and solder)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/26 15:37
-	9392	(semiconductor adj substrate) near10 (integrated adj circuit)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/26 15:42
-	1767	(semiconductor adj substrate) near10 (silicon adj wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/26 15:44

-	3221	(semiconductor adj substrate) near10 (glass)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/26 15:47
-	7	((semiconductor adj substrate) near10 (integrated adj circuit)) and ((semiconductor adj substrate) near10 (silicon adj wafer)) and ((semiconductor adj substrate) near10 (glass))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/26 15:54
-	2	6445436.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/26 15:55
-	0	(micro adj display) near10 (uniform adj image)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/26 15:57
-	3	(liquid adj crystal adj displays) near10 (uniform adj image)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/26 15:58
-	0	"6177288.did."	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/26 16:03
-	2	6177288.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/26 16:03
-	3	sojourner-douglas.IN. and (micro adj displays)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/03 09:34
-	5875	micro near10 display	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/30 14:08
-	30228	349$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/30 14:09
-	379	(micro near10 display) and 349$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/30 14:10
-	0	(micro near10 display) near10 349$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/30 14:11
-	477	(manufacturing or making or method) near10 (micro near10 display)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/30 14:12

-	49	((manufacturing or making or method) near10 (micro near10 display)) and 349$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/30 14:12
-	2	6562640.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/04 10:17
-	6276	((micro near10 display) or microdisplay)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/04 10:30
-	312132	liquid near10 crystal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/04 10:33
-	202	(making or manufactur$3) near10 (liquid near10 crystal) near10 (((micro near10 display) or microdisplay))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/04 10:36
-	319670	semiconductor near10 substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/04 10:39
-	388883	integrated near10 circuit	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/04 10:42
-	70818	silicon near10 wafer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/04 10:45
-	382	(semiconductor near10 substrate) near10 (integrated near10 circuit) near10 (silicon near10 wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/04 10:48
-	0	((making or manufactur$3) near10 (liquid near10 crystal) near10 (((micro near10 display) or microdisplay))) near10 ((semiconductor near10 substrate) near10 (integrated near10 circuit) near10 (silicon near10 wafer))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/04 10:48
-	2	((making or manufactur$3) near10 (liquid near10 crystal) near10 (((micro near10 display) or microdisplay))) and ((semiconductor near10 substrate) near10 (integrated near10 circuit) near10 (silicon near10 wafer))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/04 10:49
-	10929	(semiconductor near10 substrate) and (integrated near10 circuit) and (silicon near10 wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/04 10:51
-	382	((semiconductor near10 substrate) near10 (integrated near10 circuit) near10 (silicon near10 wafer)) and ((semiconductor near10 substrate) and (integrated near10 circuit) and (silicon near10 wafer))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/04 10:52

-	30494	349$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/04 10:53
-	3	(((semiconductor near10 substrate) near10 (integrated near10 circuit) near10 (silicon near10 wafer)) and ((semiconductor near10 substrate) and (integrated near10 circuit) and (silicon near10 wafer))) and 349$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/04 10:54
-	2	"6562640"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/04 10:55